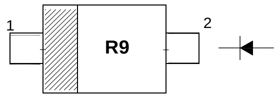
SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

Applications

- High speed switching

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



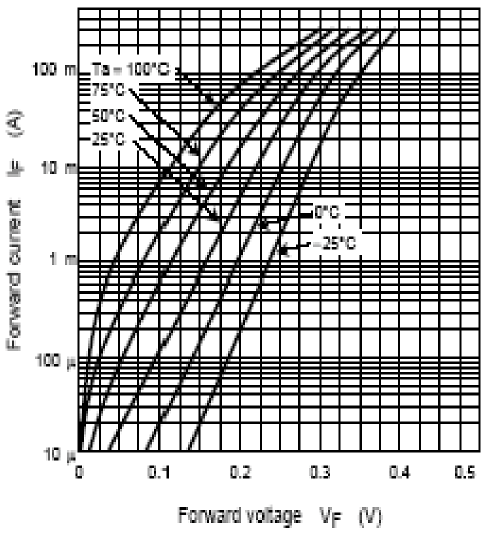
Top View
Marking Code: "**R9**"
Simplified outline SOD-323 and symbol

Absolute Maximum Ratings (T_a = 25 °C)

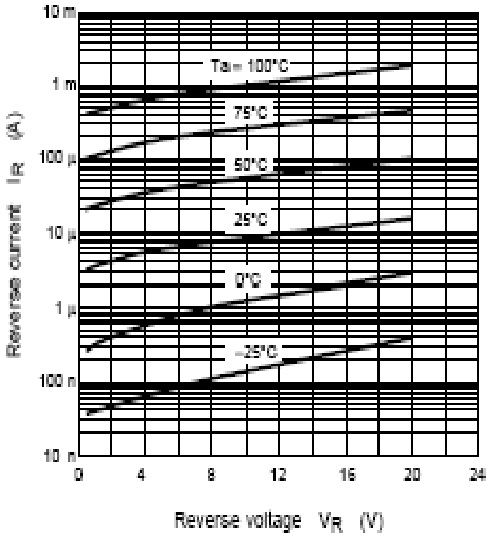
Parameter	Symbol	Value	Unit
Maximum (Peak) Reverse Voltage	V_{RM}	25	V
Reverse Voltage	V_R	20	V
Average Forward Current	I_O	300	mA
Maximum (Peak) Forward Current	I_{FM}	700	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_J	125	°C
Storage Temperature Range	T_{stg}	- 55 to + 125	°C

Characteristics at T_a = 25 °C

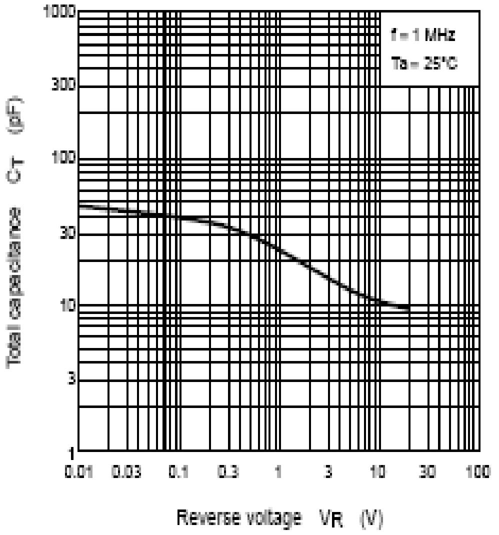
Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at I_F = 300 mA	V_F	-	0.45	V
Reverse Current at V_R = 20 V	I_R	-	50	µA
Total Capacitance at f = 1 MHz	C_T	46	-	pF



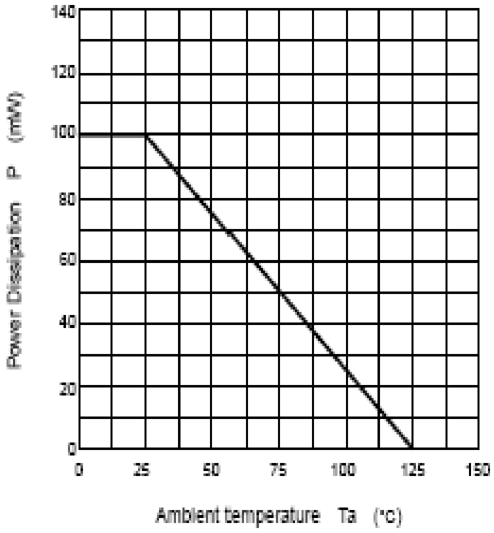
$I_F - V_F$



$I_R - V_R$



$C_T - V_R$



$P - T_a$